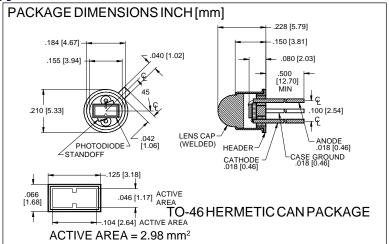
**PHOTONIC** Silicon Photodiode, Blue Enhanced Photoconductive DETECTORS INC. **Isolated Lens Type PDB-C104-IL** 





# **FEATURES**

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

## **DESCRIPTION**

The PDB-C104-IL is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-46 metal can with a glass lens cap and isolated ground

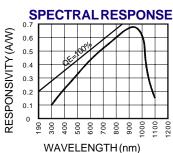
# **APPLICATIONS**

- Instrumentation
- Character recognition
- Laser detection
- Fiber optic

# ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
$V_{\mathtt{BR}}$	Reverse Voltage		100	V	
T <sub>STG</sub>	Storage Temperature	-55	+150	∘C	
T <sub>o</sub>	Operating Temperature Range	-40	+125	∘C	
T <sub>s</sub>	Soldering Temperature*		+240	∘C	
IL	Light Current		0.5	mA	

<sup>\*1/16</sup> inch from case for 3 secs max



## **ELECTRO-OPTICAL CHARACTERISTICS** (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>sc</sub>	Short Circuit Current	H = 100 fc, 2850 K	85	100		m A
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 10 V		.15	1.0	nA
R <sub>SH</sub>	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	.5	1.0		GΩ
TCR <sub>SH</sub>	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/°C
C <sub>J</sub>	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V**		10		pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 <b>m</b> A	70	100		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		1.5x10 <sup>-14</sup>		W/ √Hz
tr	Response Time	$RL = 1 K\Omega V_R = 50 V$		10		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. \*\* f = 1 MHz [FORM NO. 100-PDB-C104-IL REV N/C]